

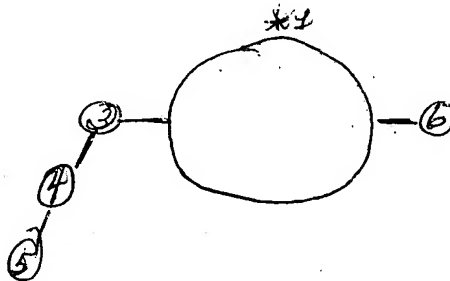
506, 534
 10/1000000

Examiner's Notes

- s (clean? (a) steps or clean? (10a) steps)
- s (reduce? or lower? or decrease? or eliminate?) (10a) (not from or diffusion or height)
- s (silicon) (10a) (single (w) crystal? or mono (w) crystal?)
- s (RTA)
- s (thermal) (8a) (process)
- s (anneal?)
- s (hydrogen)
- s (temperature)

112#2 Bej

86,
 Claim 3, lines 15, "... silicon-type point defect..." (Cite case law)
 Claim 3, lines 16, 17, "... vacancy-type point defect..." (Cite case law)



Motivation: In order to provide a method for manufacturing a di-
 single-crystal layer of which surface quality is improved & a di-
 single-crystal layer is manufactured.

8,081) [51, 24 are]

2) [Crystallization apparatus]

App
II

3) [422]

4) [245, 1]

5) [5 25 - 64 are]

6) [A unit for crystallizing a molecule (S) ...]

MD
II

7) [117]

8) [86]